Marubeni

Lead (Pb) Free Product – RoHS Compliant

SPECIFICATION OF LED CHIP
CN870-55
[INFRARED]

1) Commodity Type and Physical Characteristics.

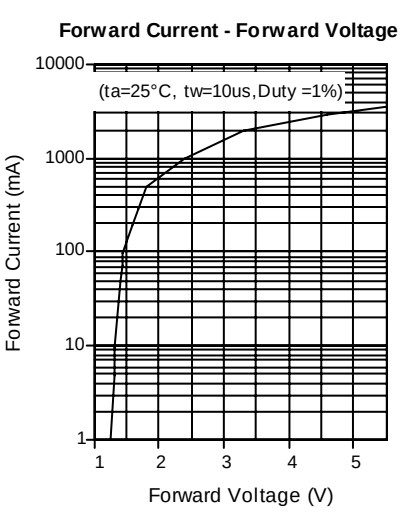
1. Material		GaAlAs/GaAlAs (DDH)
2. Electrode	Top Side	P (anode) side : Au Alloy
	Bottom Side	N (cathode) side : Au Alloy
3. Electrode Pattern	120um dia.	
4. Chip Size	550um*550um	
5. Chip Thickness	150um±30um	

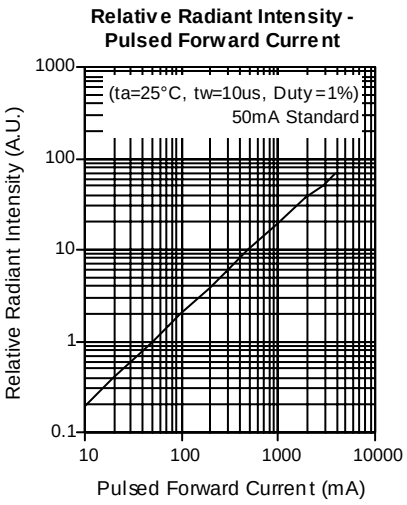
2) Electro-Optical Characteristics

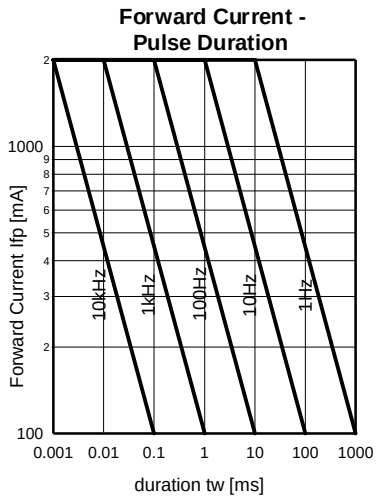
Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=50mA		1.40	1.45	V
		If=100mA		1.48	1.50	
		If=1A*		2.4	3.0	
		If=2A*		3.3	4.0	
Reverse Current	Ir	Vr=5V			10	uA
Total Radiated Power	Po	If=50mA		10		mW
		If=100mA		20		
		If=1A*		200		
		If=2A*		400		
Peak Wavelength	λP	If=50mA		870		nm
Spectral Radiation Bandwidth	Δλ	If=50mA		40		nm
RiseTime	tr	If=50mA		15		ns
FallTime	tf	If=50mA		10		ns

‡*Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡ Die shall be mounted on TO-18 gold header without resin coated. (Ta=25℃)







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